

Title (en)
MICRO-ELECTROMECHANICAL SEMICONDUCTOR COMPONENT AND METHOD FOR THE PRODUCTION THEREOF

Title (de)
MIKROELEKTROMECHANISCHES HALBLEITERBAUELEMENT UND VERFAHREN ZU SEINER HERSTELLUNG

Title (fr)
COMPOSANT SEMI-CONDUCTEUR MICROÉLECTROMÉCANIQUE ET SON PROCÉDÉ DE FABRICATION

Publication
EP 2524198 B1 20140709 (DE)

Application
EP 11700061 A 20110110

Priority
• EP 10150405 A 20100111
• EP 2011050212 W 20110110
• EP 11700061 A 20110110

Abstract (en)
[origin: WO2011083158A2] The micro-electromechanical semiconductor component is provided with a semiconductor substrate (16) in which a cavity (18) is formed, which is delimited by lateral walls (18a) and by a ceiling and a floor wall (18c, 18b). In order to form a flexible connection to the region of the semiconductor substrate (16), the ceiling or floor wall (18c, 18b) is provided with grooves (19) around the cavity (18), and flexible webs (20) are formed between said grooves. At least one measuring element (22) that is sensitive to mechanical stresses is formed inside at least one of said flexible webs (20). Inside the central region (21) surrounded by the grooves (19), the ceiling or floor wall (18c, 18b) comprises a plurality of depressions (97a) reducing the mass of the central region (21) and a plurality of stiffening braces (97b) separating the depressions (97a).

IPC 8 full level
G01L 9/00 (2006.01); **B81C 3/00** (2006.01)

CPC (source: EP US)
B81B 3/0018 (2013.01 - US); **B81B 3/0021** (2013.01 - US); **B81B 3/007** (2013.01 - EP US); **B81B 3/0072** (2013.01 - EP US); **B81B 3/0081** (2013.01 - US); **B81C 1/00158** (2013.01 - EP US); **B81C 1/00626** (2013.01 - EP US); **B81C 99/0035** (2013.01 - EP US); **G01L 9/0047** (2013.01 - EP US); **H01L 29/4916** (2013.01 - US); **B81B 2201/0235** (2013.01 - EP US); **B81B 2201/0264** (2013.01 - EP US); **B81B 2203/0127** (2013.01 - EP US); **B81C 2201/019** (2013.01 - EP US); **H01L 29/84** (2013.01 - US)

Cited by
DE102020123930B3; WO2022057970A1; EP4376303A2

Designated contracting state (EPC)
AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

DOCDB simple family (publication)
WO 2011083158 A2 20110714; WO 2011083158 A3 20111110; CN 102741674 A 20121017; CN 102741979 A 20121017; CN 102741979 B 20150729; CN 102742012 A 20121017; CN 102742012 B 20150812; EP 2523895 A2 20121121; EP 2523895 B1 20140604; EP 2523896 A2 20121121; EP 2523896 B1 20140611; EP 2524198 A2 20121121; EP 2524198 B1 20140709; EP 2524389 A2 20121121; EP 2524389 B1 20160615; EP 2524390 A2 20121121; EP 2524390 B1 20140827; US 2013087864 A1 20130411; US 2013087865 A1 20130411; US 2013087866 A1 20130411; US 2013193529 A1 20130801; US 2013200439 A1 20130808; US 2015158717 A1 20150611; US 2015166327 A1 20150618; US 8841156 B2 20140923; US 8975671 B2 20150310; US 8994128 B2 20150331; US 9013015 B2 20150421; US 9126826 B2 20150908; US 9403676 B2 20160802; US 9403677 B2 20160802; WO 2011083159 A2 20110714; WO 2011083159 A3 20111201; WO 2011083160 A2 20110714; WO 2011083160 A3 20111124; WO 2011083161 A2 20110714; WO 2011083161 A3 20111124; WO 2011083162 A2 20110714; WO 2011083162 A3 20111201

DOCDB simple family (application)
EP 2011050209 W 20110110; CN 201180005859 A 20110110; CN 201180005860 A 20110110; CN 201180005861 A 20110110; EP 11700061 A 20110110; EP 11700162 A 20110110; EP 11700163 A 20110110; EP 11700251 A 20110110; EP 11700636 A 20110110; EP 2011050210 W 20110110; EP 2011050211 W 20110110; EP 2011050212 W 20110110; EP 2011050213 W 20110110; US 201113521141 A 20110110; US 201113521146 A 20110110; US 201113521158 A 20110110; US 201113521168 A 20110110; US 201113521175 A 20110110; US 201514622075 A 20150213; US 201514631064 A 20150225